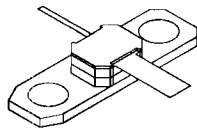
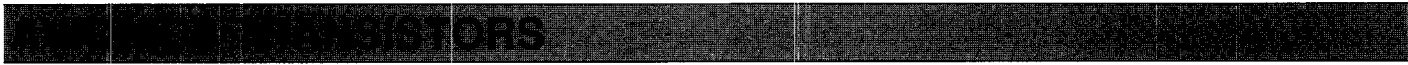
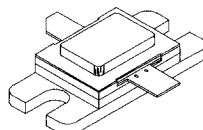


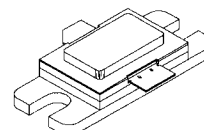
SILICON POWER TRANSISTORS



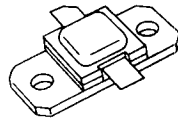
.250 SQ. 2LFL
(M105)



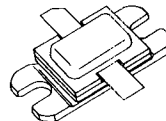
.400 x .500 2LFL
(M112)



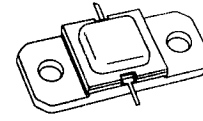
.400 x .600 2LFL
(M198)



.400 x .400 2LFL
(S036)



.400 x .500 2LFL
(S038)



.400 x .400 2NLFL
(S042)

1030/1090 MHz CLASS C, COMMON BASE, PULSED, IFF APPLICATIONS

PART NO.	FREQ. (MHz)	P _{OUT} MIN (W)	P _{IN} (W)	GAIN MIN (dB)	η _c MIN (%)	V _{CC} (V)	R _{TH(j-c)} MAX (°C/W)	PACKAGE STYLE
SD1527-08	1090	5	0.35	11.5	—	50	8.0	M105
MSC81350M	1090	350	70	6.9	40	50	0.17	S042
SD1541-09	1090	450	90	7.0	—	50	0.12	M112
SD1542-04	1090	800	150	6.0	—	50	0.06	M112
MSC81600M	1090	600	150	6.0	35	50	0.09	S038

Pulse Conditions 10μSec, 1% Duty Cycle unless otherwise specified

1030/1090 MHz CLASS C, COMMON BASE, PULSED, SPECIAL APPLICATIONS (MODE-S, TCAS)

PART NO.	FREQ. (MHz)	P _{OUT} MIN (W)	P _{IN} (W)	GAIN MIN (dB)	η _c MIN (%)	V _{CC} (V)	R _{TH(j-c)} MAX (°C/W)	PULSE WIDTH (μSEC)	DUTY CYCLE (%)	PACKAGE STYLE
AM1011-055 [†]	1090	55	6.6	9.2	48	50	1.1	32	2	S036
AM1011-075	1090	75	9	9.2	48	50	0.86	32	2	S036
AM1011-175	1090	200	32	8.0	45	50	0.28	32	2	S036
AM1011-400	1090	400	63	8.0	45	50	0.17	32	2	S038
AM1011-500	1090	500	70	8.5	40	50	0.11	32	2	M198
AM1011-070	1090	70	15	6.7	45	28	0.68	100	2	S042
AM1011-060 [†]	1030	60	8.5	8.5	45	36	—	—*	—*	S036
AM1011-225 [†]	1030	220	35	8.0	40	36	—	—*	—*	S038
AM1011-300 [†]	1030	300	55	7.3	40	36	—	—*	—*	M198

[†] In Development * Tested under pulse conditions equivalent to Mode-S ground interrogator